

Monday, September 28

9:00- Opening Session/Award Ceremony/Plenary Session (Main Hall A,B)

Lunch													
1F Middle-Sized Hall A	1F Middle-Sized Hall B	1F 101	1F 102	1F 107a	1F 107b	1F 108a	2F 201	2F 202	2F Small Hall	2F 204	2F 206	2F 207	1F 108b
14:00-15:45 A-1:Light Sources and Related Technologies		14:00-15:45 Area10&15 C-1:Organic and Perovskite Photovoltaics		14:00-15:45 Area2&13 E-1:Carbon Interconnects	14:00-15:30 F-1:Advanced Vision & Imaging Circuits	14:00-15:45 G-1:Wide-gap Materials		14:00-15:30 J-1:Device and Characterization	14:00-15:50 K-1:Tunnel FET	14:00-15:45 M-1:High-Speed & High-Frequency Devices	14:00-15:30 N-1:Junction Technology	14:00-15:30 O-1:CBRAM and IGZO Memory	14:00-15:45 P-1:Spin-orbit Effect and Application for Sensors
Coffee Break													
16:05-17:50 Area7&12 A-2:MO and EO Devices			16:05-17:50 D-2:2D Material-based Devices	16:05-18:05 E-2: Interconnects and Bonding	16:05-17:55 Area5&11 F-2:Advanced Imaging & Measurement Circuits for Bio and Medical Applications			16:05-17:05 J-2:Process and Characterization	16:05-17:50 K-2:Ge / III-V	16:05-17:50 M-2:GaN FETs	16:05-17:05 N-2:Process for Fully-Depleted Devices	16:05-17:55 Area4&8 O-2:Nano Engineered Thin Oxide Film	

19:00 - 21:00 Banquet (Royton Sapporo Hotel / Royton Hall)

Tuesday, September 29

Lunch													
1F Middle-Sized Hall A	1F Middle-Sized Hall B	1F 101	1F 102	1F 107a	1F 107b	1F 108a	2F 201	2F 202	2F Small Hall	2F 204	2F 206	2F 207	1F 108b
9:00-10:45 Area2&7 A-3:Optical Interconnection		9:00-10:30 C-3:Thin-film Photovoltaics	9:00-10:30 D-3:Nanocarbon-based Devices		9:00-10:45 F-3:Microfluidics	9:00-10:45 G-3:Dots and Non-structures	9:00-10:45 H-3:Novel Functional Devices		9:00-10:30 K-3:Characterization I	9:00-10:30 Area6&14 M-3:SiC & GaN Power Devices	9:00-10:30 N-3:Advanced Process and Characterization	9:00-10:50 O-3:ReRAM 1	9:00-10:45 P-3:Semiconductor and RF Spintronics
Coffee Break													
11:00-12:00 Short Presentation Area7		11:00-12:00 Short Presentation Area10 Short Presentation Area15	11:00-12:00 Short Presentation Area13	11:00-12:00 Short Presentation Area2	11:00-12:00 Short Presentation Area5 Short Presentation Area11	11:00-12:00 Short Presentation Area8	11:00-12:00 Short Presentation Area9	11:00-12:00 Short Presentation Area14	11:00-12:00 Short Presentation Area3	11:00-12:00 Short Presentation Area6	11:00-12:00 Short Presentation Area1	11:00-12:00 Short Presentation Area4	11:00-12:00 Short Presentation Area12

13:30-15:30 Poster Session (Main Hall A,B)

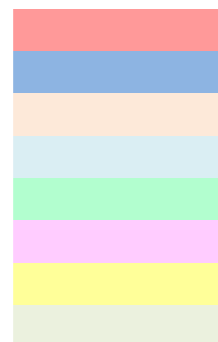
Break													
1F Middle-Sized Hall A	1F Middle-Sized Hall B	1F 101	1F 102	1F 107a	1F 107b	1F 108a	2F 201	2F 202	2F Small Hall	2F 204	2F 206	2F 207	1F 108b
15:40-16:55 A-4:Group-IV Optical Devices I	15:40-16:55 Area9&13 B-4:2D Materials I	15:40-17:10 C-4:Organic Devices I	15:40-16:55 D-4:Nanowire Devices & Characterization	15:40-16:55 E-4:MEMS and Sensor		15:40-16:55 G-4:Growth of Germanium-based Semiconductors I			15:40-16:50 K-4:CMOS	15:40-16:55 Area6&14 M-4:GaN Power Devices	15:40-17:00 N-4:Interface and Material Science	15:40-17:10 Area4&5&12 O-4:Advanced Processing Circuits with Functional Materials	
Coffee Break													
17:25-18:40 A-5:Group-IV Optical Devices II	17:25-18:40 Area9&13 B-5:2D Materials II	17:25-18:25 C-5:New Concepts			17:25-18:40 F-5:Nano Devices for Chemical & Biosensing	17:25-18:40 G-5:Growth of Germanium-based Semiconductors II			17:25-18:25 K-5:Noise	17:25-18:40 Area6&14 M-5:Novel Widegap Devices	17:25-18:55 N-5:Gate Stack Characterization	17:25-18:55 Area4&5&12 O-5:MRAM and Spintronics Logic	

19:10-20:40 Rump Sessions (Middle-Sized Hall A,B)

Wednesday, September 30

Lunch													
1F Middle-Sized Hall A	1F Middle-Sized Hall B	1F 101	1F 102	1F 107a	1F 107b	1F 108a	2F 201	2F 202	2F Small Hall	2F 204	2F 206	2F 207	1F 108b
9:00-10:00 A-6:Optical Sensing		9:00-10:00 C-6:III-V Photovoltaics and Related Technologies	9:00-10:15 Area 8&13 D-6:Nanowire Synthesis and Properties I	9:00-10:30 E-6:3D / TSV	9:00-10:20 F-6:Advanced Memories and Circuits		9:00-10:15 Area 9&12 H-6:Quantum Optics	9:00-10:15 J-6:SiC MOS	9:00-10:00 K-6:Physics	9:00-10:00 M-6:Oxide Devices	9:00-10:10 N-6:2D Materials and Band Engineering	9:00-10:30 O-6:NAND Flash Device	
Coffee Break													
10:45-12:30 A-7:III-V Devices and Related Technologies		10:45-12:30 C-7:Crystalline Silicon Photovoltaics	10:45-12:30 Area8&13 D-7:Nanowire Synthesis and Properties II	10:45-12:35 Area2&5 E-7:Advanced Circuits and MEMS Integration	10:45-12:30 F-7:Biosensors	10:45-12:45 G-7:Organic Devices II	10:45-12:30 Area9&12 H-7:Quantum Devices		10:45-12:05 K-7:Characterization II	10:45-12:30 M-7:III-V Materials & Devices		10:45-12:05 O-7:ReRAM 2	

Area Scope



- Area 1: Advanced LSI Processing & Materials Science
- Area 2: Interconnect Technologies and 3D Integration/ Sensor/ MEMS Integration/ Materials and Characterization
- Area 3: CMOS Devices / Device Physics
- Area 4: Advanced Memory Technology
- Area 5: Advanced Circuits and Systems
- Area 6: Compound Semiconductor Electron Devices & Related Technologies
- Area 7: Photonic Devices and Related Technologies
- Area 8: Advanced Material Synthesis and Crystal Growth Technology

- Area 9: Physics and Applications of Novel Functional Devices and Materials
- Area 10: Organic Materials Science, Device Physics, and Applications
- Area 11: Sensors and Materials for Biology, Chemistry and Medicine
- Area 12: Spintronics Materials and Devices
- Area 13: Applications of Nanotubes, Nanowires, and Graphene
- Area 14: Power Devices and Materials
- Area 15: Photovoltaic Materials and Devices